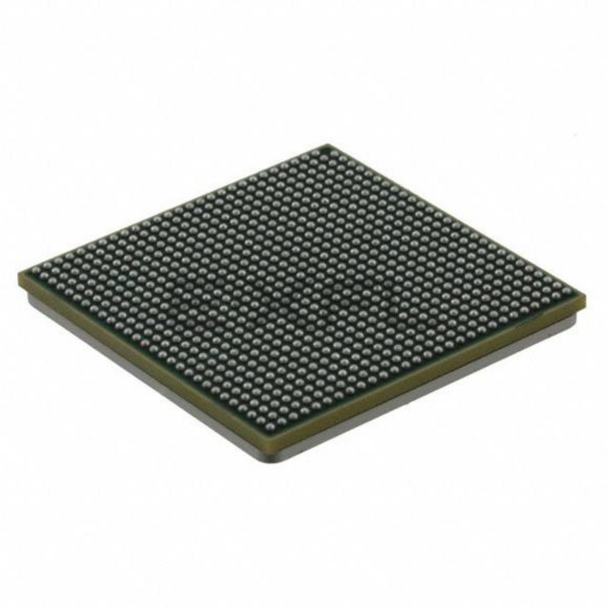
NXP USA Inc. - MPC8545EVJANGD Datasheet



Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8545evjangd

  - Memory prefetching of PCI read accesses
  - Supports posting of processor-to-PCI and PCI-to-memory writes
  - PCI 3.3-V compatible
  - Selectable hardware-enforced coherency
- Serial RapidIO™ interface unit
  - Supports *RapidIO™ Interconnect Specification, Revision 1.2*
  - Both 1× and 4× LP-serial link interfaces
  - Long- and short-haul electricals with selectable pre-compensation
  - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
  - Auto detection of 1- and 4-mode operation during port initialization
  - Link initialization and synchronization
  - Large and small size transport information field support selectable at initialization time
  - 34-bit addressing
  - Up to 256 bytes data payload
  - All transaction flows and priorities
  - Atomic set/clr/inc/dec for read-modify-write operations
  - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
  - Receiver-controlled flow control
  - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
  - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
  - Hardware recovery only
  - Register support is not required for software-mediated error recovery.
  - Accept-all mode of operation for fail-over support
  - Support for RapidIO error injection
  - Internal LP-serial and application interface-level loopback modes
  - Memory and PHY BIST for at-speed production test
- RapidIO-compatible message unit
  - 4 Kbytes of payload per message
  - Up to sixteen 256-byte segments per message
  - Two inbound data message structures within the inbox
  - Capable of receiving three letters at any mailbox
  - Two outbound data message structures within the outbox
  - Capable of sending three letters simultaneously
  - Single segment multicast to up to 32 devIDs
  - Chaining and direct modes in the outbox

Table 1. Absolute Maximum Ratings [1] (continued)

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The –0.3 to 2.75 V range is for DDR and –0.3 to 1.98 V range is for DDR2.
3. The 3.63 V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75 V maximum applies. See Section 8.2, “FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications,” for details on the recommended operating conditions per protocol.
4. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD}	1.1 V ± 55 mV	V	—
PLL supply voltage		AV_{DD}	1.1 V ± 55 mV	V	1
Core power supply for SerDes transceivers		SV_{DD}	1.1 V ± 55 mV	V	—
Pad power supply for SerDes transceivers		XV_{DD}	1.1 V ± 55 mV	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	4
		TV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	—	4
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	3
Local bus I/O voltage		BV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	—
Input voltage	DDR and DDR2 DRAM signals	MV_{IN}	GND to GV_{DD}	V	2
	DDR and DDR2 DRAM reference	MV_{REF}	GND to $GV_{DD}/2$	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	3

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices is shown in the following table.

Table 4. Device Power Dissipation

CCB Frequency[1]	Core Frequency	SLEEP[2]	Typical-65[3]	Typical-105[4]	Maximum[5]	Unit
400	800	2.7	4.6	7.5	8.1	W
	1000	2.7	5.0	7.9	8.5	W
	1200	2.7	5.4	8.3	8.9	
500	1500	11.5	13.6	16.5	18.6	W
533	1333	6.2	7.9	10.8	12.8	W

Notes:

1. CCB frequency is the SoC platform frequency, which corresponds to the DDR data rate.
2. SLEEP is based on V_{DD} = 1.1 V, T_j = 65°C.
3. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65°C, running Dhrystone.
4. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105°C, running Dhrystone.
5. Maximum is based on V_{DD} = 1.1 V, T_j = 105°C, running a smoke test.

4.3 eTSEC Gigabit Reference Clock Timing

The following table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the device.

Table 6. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	
EC_GTX_CLK125 rise and fall time L/TVDD = 2.5 V L/TVDD = 3.3 V	t_{G125R}, t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2, 3

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TV$_{DD}$ = 2.5 V, and from 0.6 and 2.7 V for L/TV$_{DD}$ = 3.3 V.
2. Timing is guaranteed by design and characterization.
3. EC_GTX_CLK125 is used to generate the GTX clock TSEC*n*_GTX_CLK for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the TSEC*n*_ GTX_CLK. See Section 8.2.6, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 PCI/PCI-X Reference Clock Timing

When the PCI/PCI-X controller is configured for asynchronous operation, the reference clock for the PCI/PCI-x controller is not the SYSCLK input, but instead the PCI*n*_CLK. The following table provides the PCI/PCI-X reference clock AC timing specifications for the device.

Table 7. PCI*n*_CLK AC Timing Specifications

At recommended operating conditions (see Table 2) with OV$_{DD}$ = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
PCI*n*_CLK frequency	f_{PCICLK}	16	—	133	MHz	—
PCI*n*_CLK cycle time	t_{PCICLK}	7.5	—	60	ns	—
PCI*n*_CLK rise and fall time	t_{PCIKH}, t_{PCIKL}	0.6	1.0	2.1	ns	1, 2
PCI*n*_CLK duty cycle	$t_{PCIKHKL}/t_{PCICLK}$	40	—	60	%	2

Notes:

1. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
2. Timing is guaranteed by design and characterization.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface. The DDR controller supports both DDR1 and DDR2 memories. DDR1 is supported with the following AC timings at data rates of 333 MHz. DDR2 is supported with the following AC timings at data rates down to 333 MHz.

6.2.1 DDR SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 1.8 V.

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions

Parameter	Symbol	Min	Max	Unit
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V

Table 17 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 2.5 V.

Table 17. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V

This table provides the input AC timing specifications for the DDR SDRAM interface.

Table 18. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}			ps	1, 2
533 MHz					
400 MHz		–300	300		
333 MHz		–365	365		
		–390	390		

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This must be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: $t_{DISKEW} = \pm (T/4 - \text{abs}(t_{CISKEW}))$ where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAS}	1.48 1.95 2.40	— — —	ns	3
ADDR/CMD output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAX}	1.48 1.95 2.40	— — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCS}	1.48 1.95 2.40	— — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCX}	1.48 1.95 2.40	— — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS 533 MHz 400 MHz 333 MHz	$t_{DDKHDS,}$ t_{DDKLDS}	538 700 900	— — —	ps	5
MDQ/MECC/MDM output hold with respect to MDQS 533 MHz 400 MHz 333 MHz	$t_{DDKHDX,}$ t_{DDKLDX}	538 700 900	— — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

A timing diagram for TBI receive appears in Figure 16.

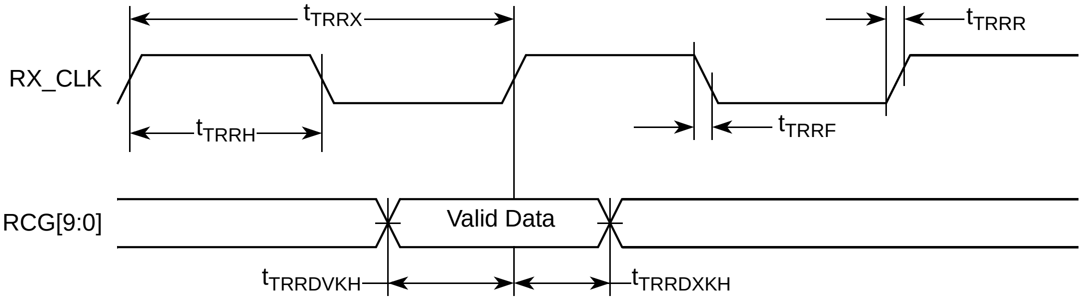


Figure 16. TBI Single-Clock Mode Receive AC Timing Diagram

8.2.6 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

Table 33. RGMII and RTBI AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}[5]	–500[6]	0	500[6]	ps
Data to clock input skew (at receiver) [2]	t_{SKRGT}	1.0	—	2.8	ns
Clock period [3]	t_{RGT}[5]	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX[3, 4]	t_{RGTH}/t_{RGT}[5]	45	50	55	%
Rise time (20%–80%)	t_{RGTR}[5]	—	—	0.75	ns
Fall time (20%–80%)	t_{RGTF}[5]	—	—	0.75	ns

Notes:

1. In general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
5. Guaranteed by characterization.
6. In rev 1.0 silicon, due to errata, t_{SKRGT} is -650 ps (min) and 650 ps (max). See “eTSEC 10” in the device errata document.

NOTE

PLL bypass mode is required when LBIU frequency is at or below 83 MHz. When LBIU operates above 83 MHz, LBIU PLL is recommended to be enabled.

Figure 23 through Figure 28 show the local bus signals.

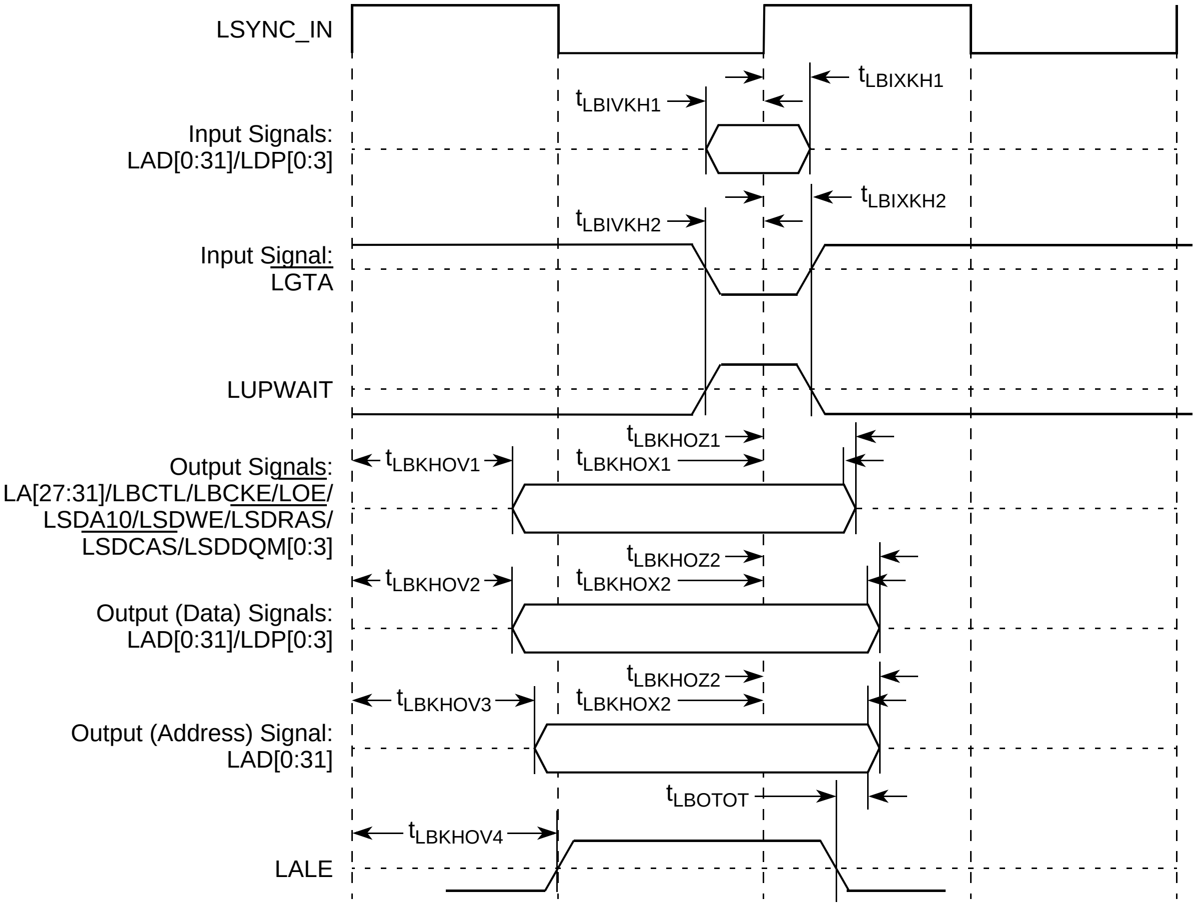


Figure 23. Local Bus Signals (PLL Enabled)

This table describes the timing parameters of the local bus interface at BV_{DD} = 3.3 V with PLL disabled.

Table 42. Local Bus Timing Parameters—PLL Bypassed

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	12	—	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
Internal launch/capture clock to LCLK delay	t_{LBKHKT}	2.3	4.4	ns	8
Input setup to local bus clock (except $\overline{LGTA}$/LUPWAIT)	$t_{LBIVKH1}$	6.2	—	ns	4, 5
$\overline{LGTA}$/LUPWAIT input setup to local bus clock	$t_{LBIVKL2}$	6.1	—	ns	4, 5
Input hold from local bus clock (except $\overline{LGTA}$/LUPWAIT)	$t_{LBIXKH1}$	–1.8	—	ns	4, 5

Table 42. Local Bus Timing Parameters—PLL Bypassed (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKL2}$	–1.3	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKLOV1}$	—	–0.3	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKLOV2}$	—	–0.1	ns	4
Local bus clock to address valid for LAD	$t_{LBKLOV3}$	—	0	ns	4
Local bus clock to LALE assertion	$t_{LBKLOV4}$	—	0	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKLOX1}$	–3.7	—	ns	4
Output hold from local bus clock for LAD/LDP	$t_{LBKLOX2}$	–3.7	—	ns	4
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKLOZ1}$	—	0.2	ns	7
Local bus clock to output high impedance for LAD/LDP	$t_{LBKLOZ2}$	—	0.2	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to local bus clock for PLL bypass mode. Timings may be negative with respect to the local bus clock because the actual launch and capture of signals is done with the internal launch/capture clock, which precedes LCLK by t_{LBKHKT}.
3. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
4. All signals are measured from $BV_{DD}/2$ of the rising edge of local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
5. Input timings are measured at the pin.
6. The value of t_{LBOTOT} is the measurement of the minimum time between the negation of LALE and any change in LAD.
7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
8. Guaranteed by characterization.
9. Guaranteed by design.

13 I^2C

This section describes the DC and AC electrical characteristics for the I^2C interfaces of the device.

13.1 I^2C DC Electrical Characteristics

This table provides the DC electrical characteristics for the I^2C interfaces.

Table 45. I^2C DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	3
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. See the *MPC8548E PowerQUICC™ III Integrated Processor Family Reference Manual*, for information on the digital filter used.
3. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

13.2 I^2C AC Electrical Specifications

This table provides the AC timing parameters for the I^2C interfaces.

Table 46. I^2C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit	Notes
SCL clock frequency	f_{I2C}	0	400	kHz	—
Low period of the SCL clock	t_{I2CL}	1.3	—	μs	4
High period of the SCL clock	t_{I2CH}	0.6	—	μs	4
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs	4
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs	4
Data setup time	t_{I2DVKH}	100	—	ns	4
Data input hold time:	t_{I2DXKL}			μs	2
CBUS compatible masters		—	—		
I^2C bus devices		0	—		
Data output delay time:	t_{I2OVKL}	—	0.9	—	3
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs	—
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs	—

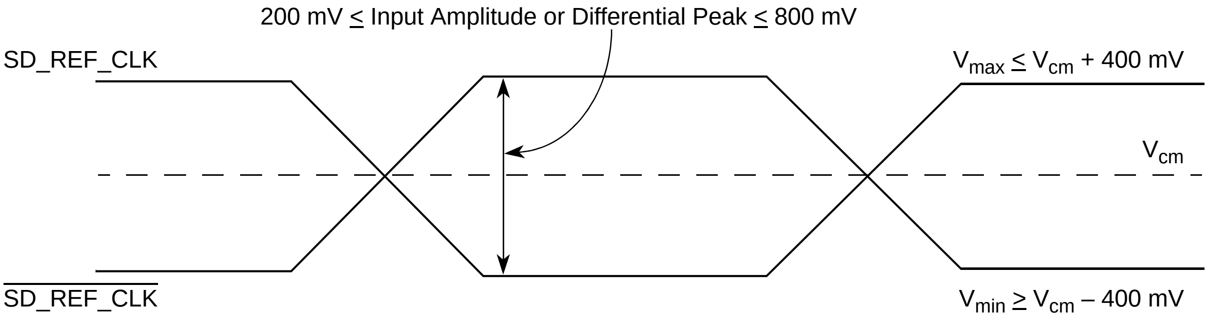


Figure 41. Differential Reference Clock Input DC Requirements (External AC-Coupled)

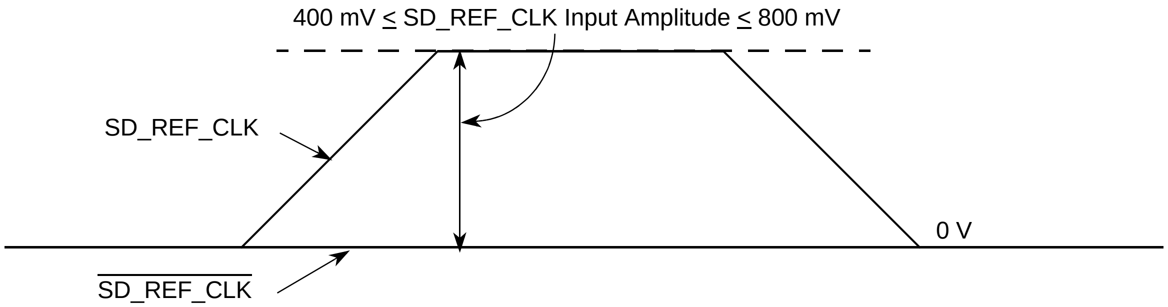


Figure 42. Single-Ended Reference Clock Input DC Requirements

16.2.3 Interfacing with Other Differential Signaling Levels

- With on-chip termination to SGND_SRDSn (xcorevss), the differential reference clocks inputs are HCSL (high-speed current steering logic) compatible DC-coupled.
- Many other low voltage differential type outputs like LVDS (low voltage differential signaling) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100 to 400 mV) for DC-coupled connection.
- LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

NOTE

Figure 43 through Figure 46 below are for conceptual reference only. Due to the fact that clock driver chip's internal structure, output impedance, and termination requirements are different between various clock driver chip manufacturers, it is very possible that the clock circuit reference designs provided by clock driver chip vendor are different from what is shown below. They might also vary from one vendor to the other. Therefore, Freescale Semiconductor can neither provide the optimal clock driver reference circuits, nor guarantee the correctness of the following clock driver connection reference circuits. The system designer is recommended to contact the selected clock driver chip vendor for the optimal reference circuits with the SerDes reference clock receiver requirement provided in this document.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50. to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50-Ω probes—see Figure 50). Note that the series capacitors, CTX, are optional for the return loss measurement.

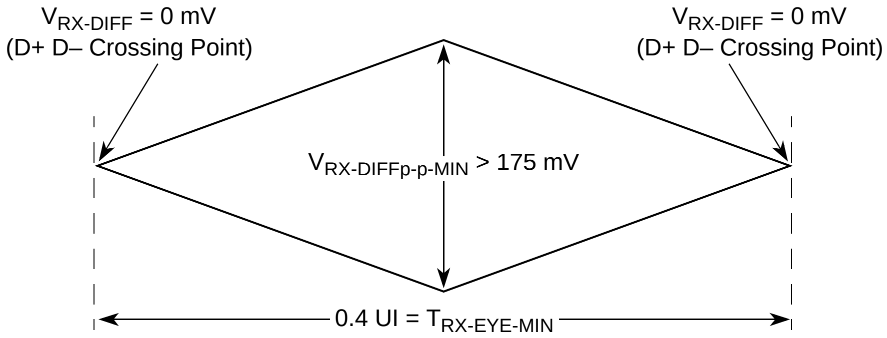


Figure 49. Minimum Receiver Eye Timing and Voltage Compliance Specification

17.5.1 Compliance Test and Measurement Load

The AC timing and voltage parameters must be verified at the measurement point, as specified within 0.2 inches of the package pins, into a test/measurement load shown in Figure 50.

NOTE

The allowance of the measurement point to be within 0.2 inches of the package pins is meant to acknowledge that package/board routing may benefit from D+ and D– not being exactly matched in length at the package pin boundary.

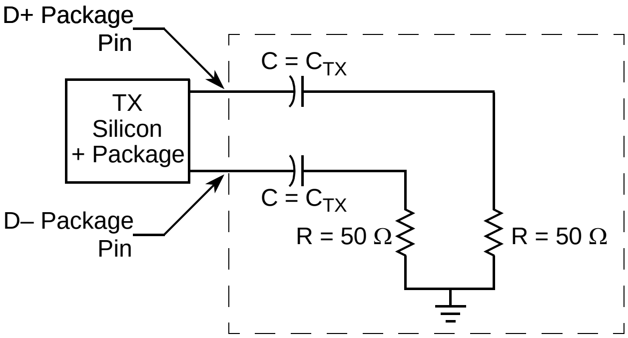


Figure 50. Compliance Test/Measurement Load

18 Serial RapidIO

This section describes the DC and AC electrical specifications for the RapidIO interface of the MPC8548E, for the LP-Serial physical layer. The electrical specifications cover both single- and multiple-lane links. Two transmitters (short and long run) and a single receiver are specified for each of three baud rates, 1.25, 2.50, and 3.125 GBaud.

Two transmitter specifications allow for solutions ranging from simple board-to-board interconnect to driving two connectors across a backplane. A single receiver specification is given that accepts signals from both the short- and long-run transmitter specifications.

The short-run transmitter must be used mainly for chip-to-chip connections on either the same printed-circuit board or across a single connector. This covers the case where connections are made to a mezzanine (daughter) card. The minimum swings of the short-run specification reduce the overall power used by the transceivers.

The long-run transmitter specifications use larger voltage swings that are capable of driving signals across backplanes. This allows a user to drive signals across two connectors and a backplane. The specifications allow a distance of at least 50 cm at all baud rates.

All unit intervals are specified with a tolerance of ±100 ppm. The worst case frequency difference between any transmit and receive clock is 200 ppm.

To ensure interoperability between drivers and receivers of different vendors and technologies, AC coupling at the receiver input must be used.

18.1 DC Requirements for Serial RapidIO SD_REF_CLK and SD_REF_CLK

For more information, see Section 16.2, “SerDes Reference Clocks.”

18.2 AC Requirements for Serial RapidIO SD_REF_CLK and SD_REF_CLK

Table 58 lists the Serial RapidIO SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ AC requirements.

Table 58. SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typ	Max	Unit	Comments
t_{REF}	REFCLK cycle time	—	10(8)	—	ns	8 ns applies only to serial RapidIO with 125-MHz reference clock
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles.	—	—	80	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location.	–40	—	40	ps	—

Table 60. Short Run Transmitter AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	500	1000	mV p-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	400	400	ps	±100 ppm

Table 61. Short Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	500	1000	mVp-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	320	320	ps	±100 ppm

Table 62. Long Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	800	1600	mVp-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	800	800	ps	±100 ppm

19.2 Mechanical Dimensions of the HiCTE FC-CBGA and FC-PBGA with Full Lid

The following figures show the mechanical dimensions and bottom surface nomenclature for the MPC8548E HiCTE FC-CBGA and FC-PBGA packages.

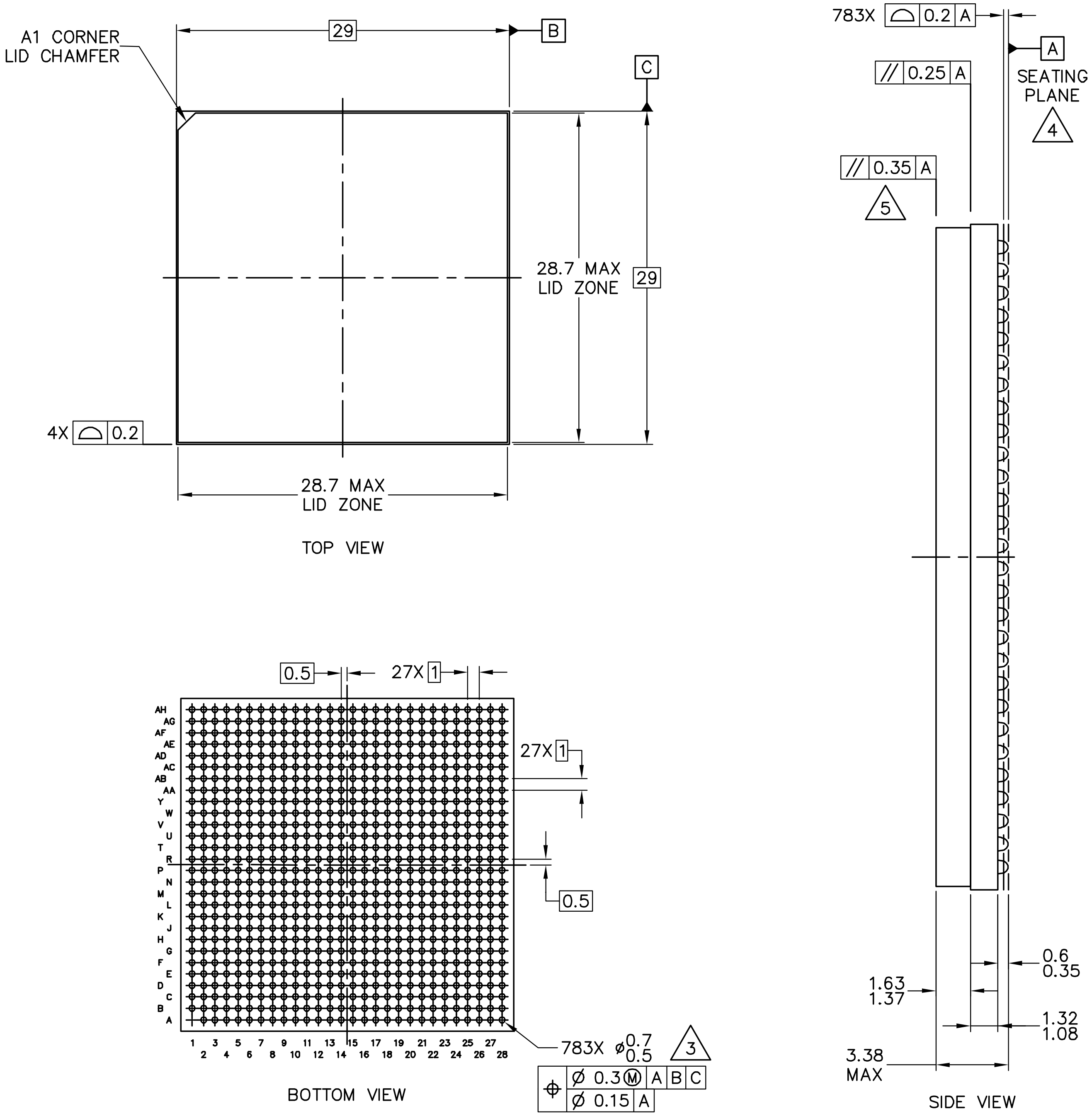


Figure 55. Mechanical Dimensions and Bottom Surface Nomenclature of the HiCTE FC-CBGA and FC-PBGA with Full Lid

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\mathrm{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV$_{DD}$	—
				—
				—
				—
				—
$\overline{\mathrm{PCI1\_REQ0}}$	AH3	I/O	OV$_{DD}$	—
PCI1_CLK	AH26	I	OV$_{DD}$	39
$\overline{\mathrm{PCI1\_DEVSEL}}$	AH11	I/O	OV$_{DD}$	2
$\overline{\mathrm{PCI1\_FRAME}}$	AE11	I/O	OV$_{DD}$	2
PCI1_IDSEL	AG9	I	OV$_{DD}$	—
$\overline{\mathrm{PCI1\_REQ64}}$/$\overline{\mathrm{PCI2\_FRAME}}$	AF14	I/O	OV$_{DD}$	2, 5, 10
$\overline{\mathrm{PCI1\_ACK64}}$/$\overline{\mathrm{PCI2\_DEVSEL}}$	V15	I/O	OV$_{DD}$	2
PCI2_CLK	AE28	I	OV$_{DD}$	39
$\overline{\mathrm{PCI2\_IRDY}}$	AD26	I/O	OV$_{DD}$	2
$\overline{\mathrm{PCI2\_PERR}}$	AD25	I/O	OV$_{DD}$	2
$\overline{\mathrm{PCI2\_GNT}}$[4:1]	AE26, AG24, AF25, AE25	O	OV$_{DD}$	5, 9, 35
$\overline{\mathrm{PCI2\_GNT0}}$	AG25	I/O	OV$_{DD}$	—
$\overline{\mathrm{PCI2\_SERR}}$	AD24	I/O	OV$_{DD}$	2, 4
$\overline{\mathrm{PCI2\_STOP}}$	AF24	I/O	OV$_{DD}$	2
$\overline{\mathrm{PCI2\_TRDY}}$	AD27	I/O	OV$_{DD}$	2
$\overline{\mathrm{PCI2\_REQ}}$[4:1]	AD28, AE27, W17, AF26	I	OV$_{DD}$	—
$\overline{\mathrm{PCI2\_REQ0}}$	AH25	I/O	OV$_{DD}$	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV$_{DD}$	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV$_{DD}$	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV$_{DD}$	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV$_{DD}$	—
$\overline{\mathrm{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV$_{DD}$	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV$_{DD}$	—
MBA[0:2]	F7, J7, M11	O	GV$_{DD}$	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1\_TRDY}}$	AG11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1\_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
cfg_pci1_width	AF14	I/O	OV_{DD}	112
Reserved	V15	—	—	110
Reserved	AE28	—	—	2
Reserved	AD26	—	—	110
Reserved	AD25	—	—	110
Reserved	AE26	—	—	110
cfg_pci1_clk	AG24	I	OV_{DD}	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	110
Reserved	AG25	—	—	110
Reserved	AD24	—	—	110
Reserved	AF24	—	—	110
Reserved	AD27	—	—	110
Reserved	AD28, AE27, W17, AF26	—	—	110
Reserved	AH25	—	—	110
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—
SD_IMP_CAL_RX	L28	I	200 Ω (±1%) to GND	—
SD_IMP_CAL_TX	AB26	I	100 Ω (±1%) to GND	—
SD_PLL_TPA	U26	O	AVDD_SRDS	24

Note: All note references in this table use the same numbers as those for Table 71. See Table 71 for the meanings of these notes.